(Tc = 25°C unless otherwise specified)

$V_{(BR)DSS}$	Drain-source breakdown voltage	1200	-	-	V	V_{GS} = 0V, I_D = 100μA	
$V_{GS(th)}$	Gate threshold voltage	2.3	2.8	3.6	V	V_{DS} = V_{GS}, I_D = 25mA	Fig.11
		-	2.2	-	V	V_{DS} = V_{GS}, I_D = 25mA, T_J = 175°C	
I_{DSS}	Zero gate voltage drain current	-	1	10	μA	V_{DS} = 1200V, V_{GS} = 0V	
I_{GSS}	Gate source leakage current	-	-	100	nA	V_{GS} = 18V, V_{DS} = 0V	
$R_{DS(on)}$	Current drain-source on-state resistance	-	12	18	mΩ	V_{GS} = 15V, I_D = 86A	Fig.4,5,6
		-	19	-		V_{GS} = 15V, I_D = 86A, T_J = 175°C	
		-	10	14		V_{GS} = 18V, I_D = 86A	
		-	18	-		V_{GS} = 18V, I_D = 86A, T_J = 175°C	
g_{fs}	Transconductance	-	71	-	S	V_{DS} = 20V, I_D = 86A	Fig.7
		-	65	-		V_{DS} = 20V, I_D = 86A, T_J = 175°C	
$R_{g,int}$	Internal gate resistance	-	7.3	-	Ω	V_{AC} = 25mV, f = 1MHz, open drain	

(Tc = 25°C unless otherwise specified)

C_{iss}	Input capacitance	-	6947	-	pF	V_{DS} = 1000V, V_{GS} = 0V T_J = 25°C, V_{AC} = 25mV f = 100kHz	Fig.17,18
C_{oss}	Output capacitance	-	247	-			
C_{rss}	Reverse capacitance	-	12	-			
E_{oss}	Coss stored energy	-	159	-	μJ		Fig.16

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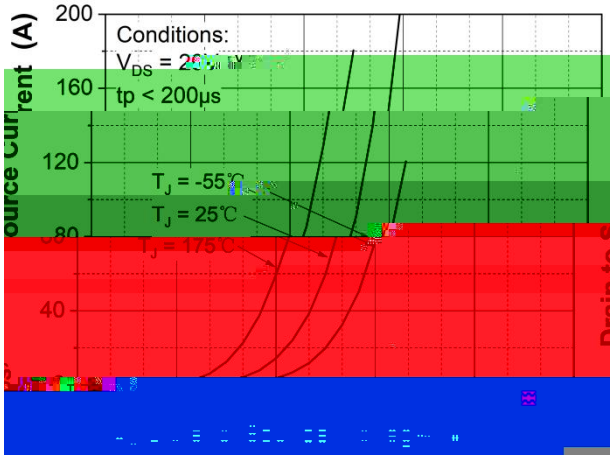


Figure 7. Transfer characteristic for various junction temperatures

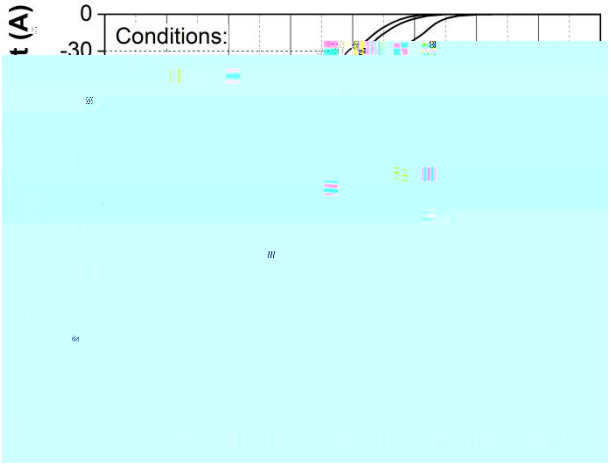


Figure 8. Body diode characteristic at T_J = -55 ºC

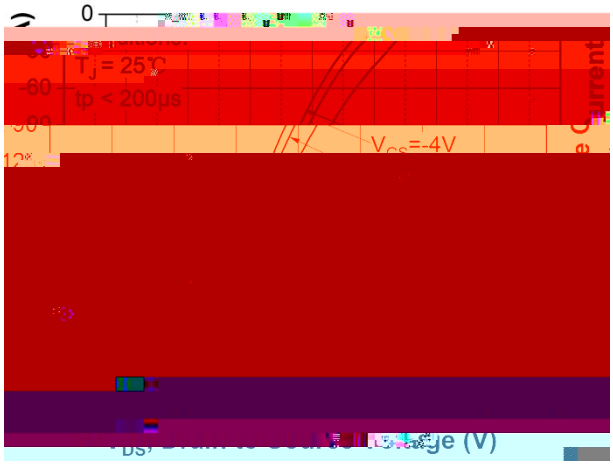


Figure 9. Body diode characteristic at T_J = 25 ºC

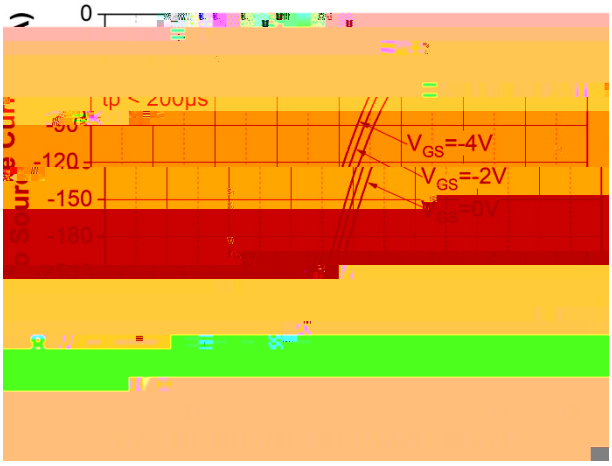


Figure 10. Body diode characteristic at T_J = 175ºC

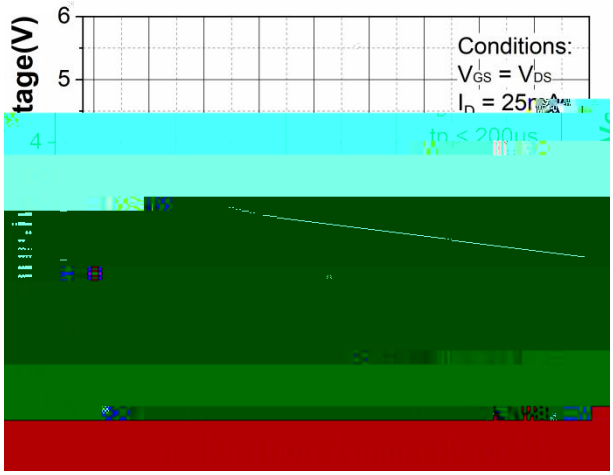


Figure 11. Threshold voltage vs. temperature

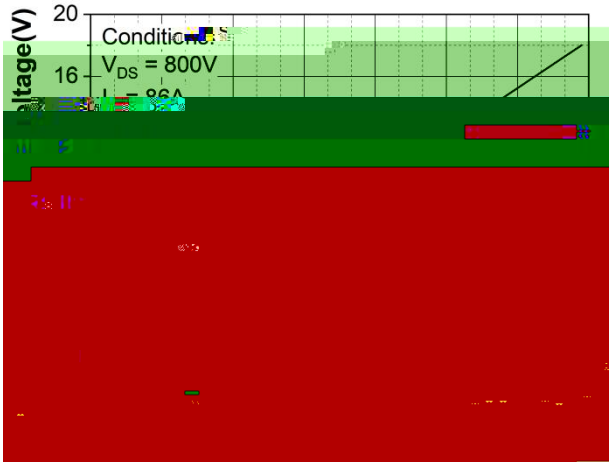


Figure 12. Gate charge characteristic

Figure 13. 3rd quadrant characteristic at T_J = -55 ºC

Figure 14. 3rd quadrant characteristic at T_J 5 m "

Die size W x L	4.80 * 6.30	mm
Gate pad size W x L	0.78 * 0.67	mm
Source pad size W x L	1.75 *4.30	mm
Kelvin pad size W x L	1.10 * :.	

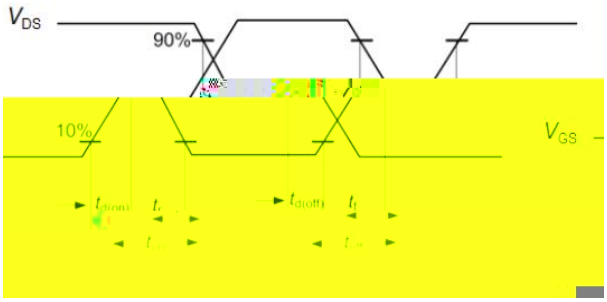


Figure A. Definition of switching times

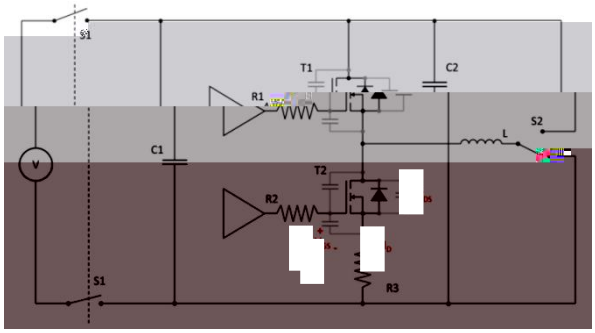


Figure B. Dynamic test circuit

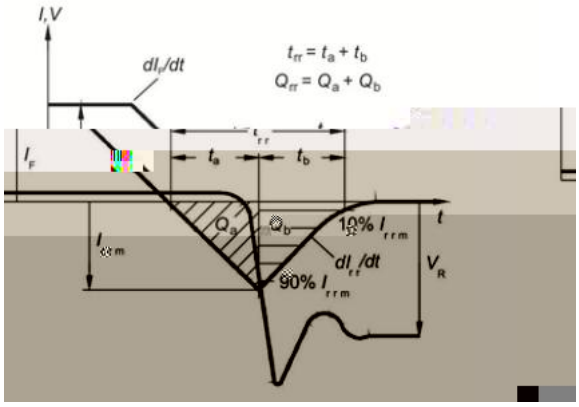


Figure C. Definition of body diode switching characteristics

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6. Due